

This listing of claims will replace all prior versions, and listings, of claims in the application:

The Status of the Claims

1. (Currently Amended) A method of manufacturing a semiconductor device comprising:
 - forming a multi-layered insulating structure on a semiconductor substrate, the multi-layered insulating structure including an upper oxide layer, an intermediate nitride layer and a lower oxide layer;
 - forming an opening in the insulating structure to expose a field region of the semiconductor substrate;
 - forming a trench in the field region of the semiconductor substrate;
 - forming a groove on an edge portion of ~~an~~ the intermediate nitride layer of the multi-layered insulating structure;
 - depositing a liner insulating layer in a desired thickness on ~~a surface of the multi-layered insulating structure~~ surfaces of the trench, on an edge of the lower oxide layer, in the groove of the edge portion of the intermediate nitride layer, and on an edge of the upper oxide layer; and
 - filling the groove and the trench with an oxide layer.

2. (Currently Cancelled)

3. (Currently Amended) A method as defined in claim 1, wherein the liner insulating layer ~~is formed of~~ comprises a liner oxide layer.

4. (Original) A method as defined in claim 3, wherein the liner oxide layer is deposited by an atomic layer deposition (ALD) process.

5. (Original) A method as defined in claim 4, wherein the liner oxide layer is deposited in a thickness of approximately 100 to 300 Å.

6. (Original) A method as defined in claim 5, wherein the liner oxide layer is deposited at a temperature of approximately 250 to 350 °C.

7. (Currently Cancelled)